

**TITLE: Removable semiconductor substrate made of polycrystalline silicon
carbide**

ABSTRACT

- 5 The present disclosure relates to an intermediate substrate (10) for manufacturing a semiconductor substrate, successively comprising:
- a. a first semiconductive layer (2);
 - b. a first thermal barrier layer (5);
 - 10 c. a support (13) comprising an absorption layer (3) configured to absorb laser radiation in a determined wavelength range, with the temperature of the absorption layer (3) increasing during absorption, and a separation zone (8) adjacent to the absorption layer (3) and configured to thermally degrade under the effect of the increase in temperature of the absorption layer, so as to separate at least part of the support (13) from the rest of the intermediate
 - 15 substrate (10).

Figure for the abstract: Figure 1